



**SDI FINAL EVALUATION FORM 1.1**

**PART 1:**

Journal Name:	<a href="#">Physical Science International Journal</a>
Manuscript Number:	2015_PSIJ_17567
Title of the Manuscript:	Modeling and Simulation of High Blocking Voltage in 4H Silicon Carbide Bipolar Junction Transistors
Type of Article	

**PART 2:**

FINAL EVALUATOR'S comments on revised paper (if any)	Authors' response to final evaluator's comments
The authors improved the paper but the presented version requires a complementary work, particularly, at the level of the paragraph 3. The authors analyzed in the paragraph 2 the transistors breakdown phenomenon, but in the paragraph 3, the author does not take it into account . This point must be analyzed in the final version.	

**Reviewer Details:**

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